MOSFETs Silicon N-channel MOS (U-MOSVII)

TPN4R203NC

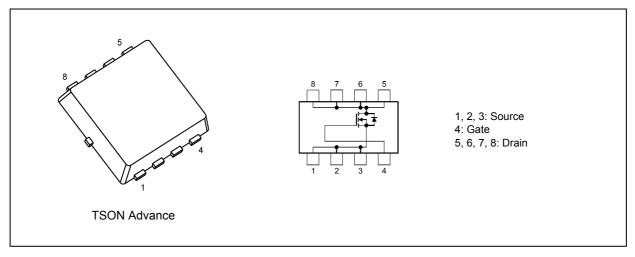
1. Applications

- Lithium-Ion Secondary Batteries
- Power Management Switches

2. Features

- (1) Small, thin package
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 3.5 \text{ m}\Omega$ (typ.) (V_{GS} = 10 V)
- (3) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 30 \ V)$
- (4) Enhancement mode: V_{th} = 1.3 to 2.3 V (V_{DS} = 10 V, I_{D} = 0.2 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25°C unless otherwise specified)

Characteris	Symbol	Rating	Unit		
Drain-source voltage			V _{DSS}	30	V
Gate-source voltage			V _{GSS}	±20	
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I _D	53	A
Drain current (DC)		(Note 1)	I _D	23	
Drain current (pulsed)	(1 ms)	(Note 1)	I _{DP}	146	
Power dissipation	(T _c = 25°C)		PD	22	W
Power dissipation	(t = 10 s)	(Note 3)	PD	1.9	
Power dissipation	(t = 10 s)	(Note 4)	PD	0.7	
Single-pulse avalanche energy		(Note 5)	E _{AS}	62	mJ
Avalanche current			I _{AR}	23	A
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	1

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

5. Thermal Characteristics

Characterist	ics		Symbol	Max	Unit
Channel-to-case thermal resistance	(T _c = 25°C)		R _{th(ch-c)}	5.68	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R _{th(ch-a)}	65.7	
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 4)	R _{th(ch-a)}	178	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Limited by silicon chip capability. Package limit is 45 A.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 0.091 mH, I_{AR} = 23 A

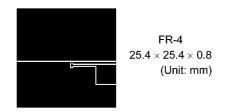


Fig. 5.1 Device Mounted on a Glass-Epoxy

Board (a)



Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

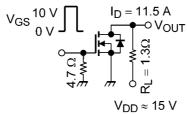
6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	_	_	±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	_		10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	30	—	—	V
Drain-source breakdown voltage (Note 6)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	15	_	—	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.2 mA	1.3	_	2.3	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 4.5 V, I _D = 11.5 A	_	5.1	6.4	mΩ
		V _{GS} = 10 V, I _D = 11.5 A		3.5	4.2	

Note 6: If a reverse bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		1370	_	pF
Reverse transfer capacitance	C _{rss}]	_	110	—	
Output capacitance	C _{oss}			420	—	
Switching time (rise time)	tr	See Figure 6.2.1.		5.0	_	ns
Switching time (turn-on time)	t _{on}]	_	13	—	
Switching time (fall time)	t _f]		14	_	
Switching time (turn-off time)	t _{off}			52	_	



Duty \leq 1%, $t_W = 10~\mu s$

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

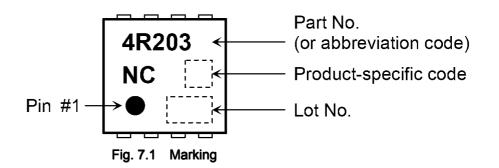
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 24$ V, V_{GS} = 10 V, I_D = 23 A	_	24	—	nC
Gate-source charge 1	Q _{gs1}]		5		
Gate-drain charge	Q _{gd}		_	4.9	_	

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

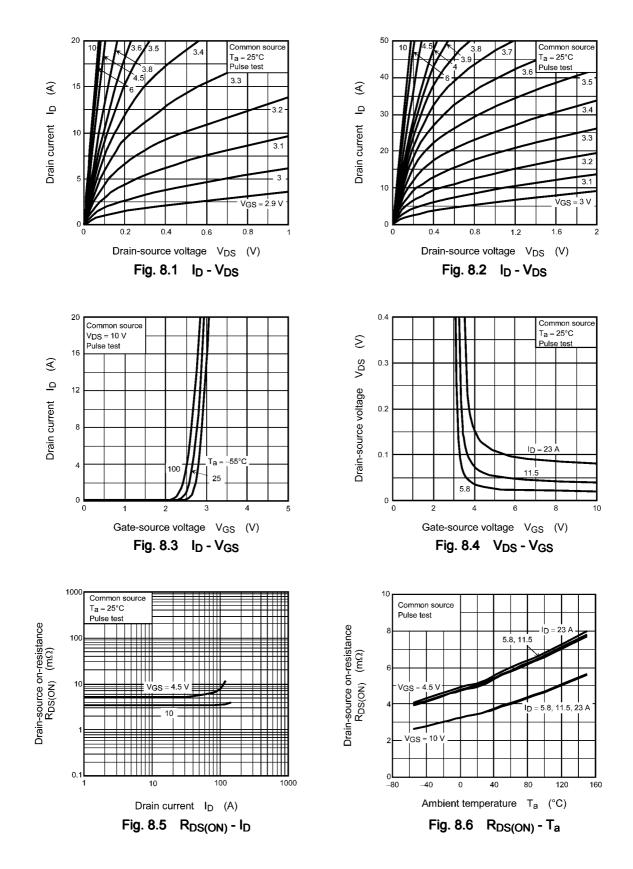
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) ((Note 7)	I _{DRP}		_	—	146	А
Diode forward voltage		V _{DSF}	I _{DR} = 23 A, V _{GS} = 0 V			-1.2	V

Note 7: Ensure that the channel temperature does not exceed 150°C.

7. Marking



8. Characteristics Curves (Note)



S

< t

Gate threshold voltage

2.5

2.0

1.5

1.0

0.5

0 -80

Common source VDS = 10 V

-40

0

Fig. 8.9 Vth - Ta

ID = 0.2 mA

Pulse test

100

30

25

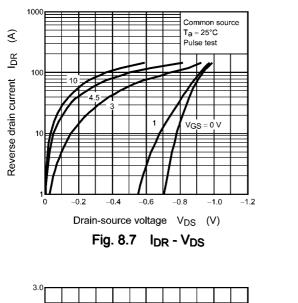
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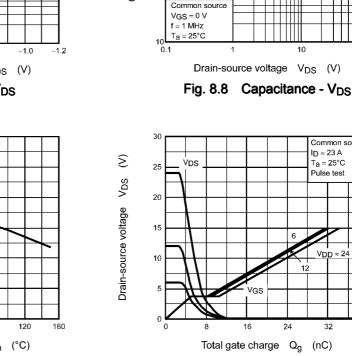
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V_{GS}

Common source ID = 23 A Ta = 25°C

Pulse test





10000

1000

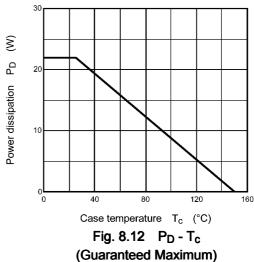
100

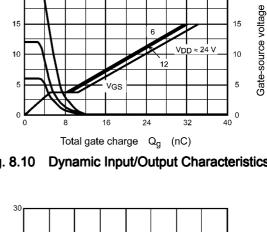
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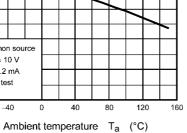
Capacitance

Fig. 8.10 Dynamic Input/Output Characteristics





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3.0 (1) Device mounted on a glass-epoxy board (a) (Note 3)
(2) Device mounted on a glass-epoxy board (b) (Note 4)
t = 10 s Ś ď 2.0 (1) Power dissipation 1.0 (2) 0 **`** 40 80 120 160 Ambient temperature Ta (°C) Fig. 8.11 P_D - T_a (Guaranteed Maximum)

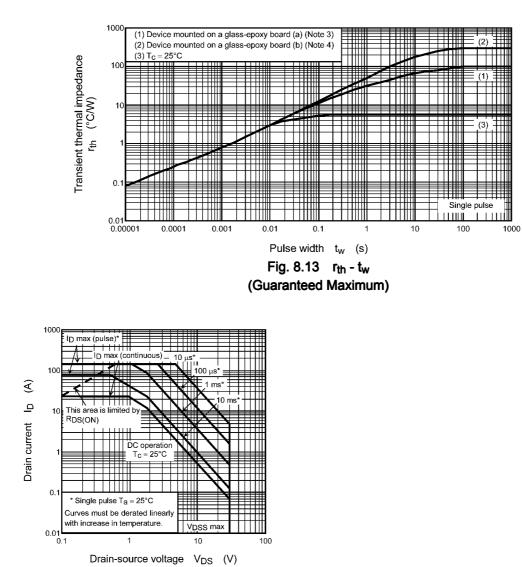


Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

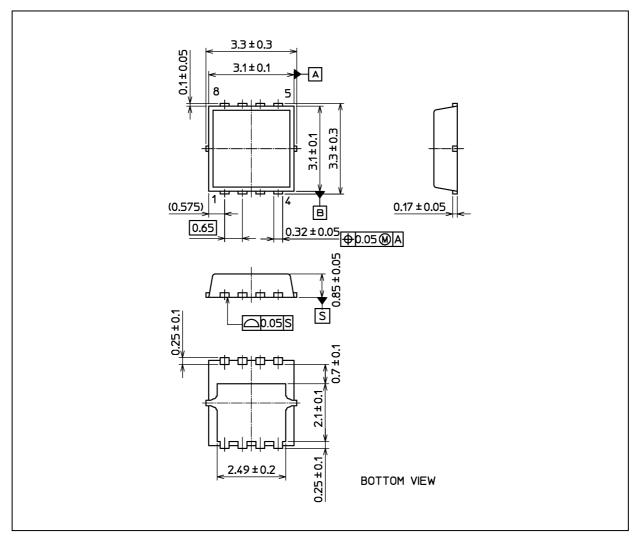
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



TPN4R203NC

Package Dimensions

Unit: mm



Weight: 0.02 g (typ.)

Package Name(s)
TOSHIBA: 2-3X1S
Nickname: TSON Advance

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